

Silicon NPN Power Transistors

MJE13007

DESCRIPTION

- With TO-220C package
- High voltage ,high speed

APPLICATIONS

- Particularly suited for 115V and 220V switchmode applications such as switching regulators,inverters ,motor controls,solenoid/ relay drivers and deflection circuits

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

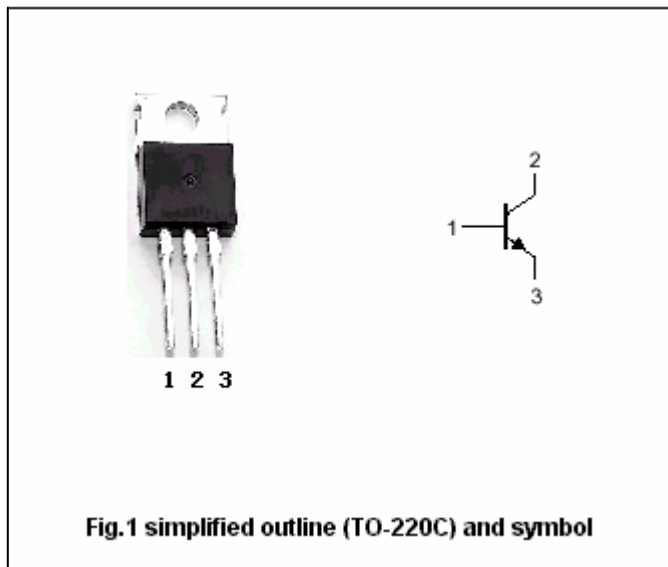


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	700	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	9	V
I _C	Collector current (DC)		8	A
I _{CM}	Collector current-Peak		16	A
I _B	Base current		4	A
I _{BM}	Base current-Peak		8	A
I _E	Emitter current		12	A
I _{EM}	Emitter current-Peak		24	A
P _D	Total power dissipation	T _C =25°C	80	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-C}	Thermal resistance from junction to case	1.56	°C/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE0(SUS)}	Collector-emitter sustaining voltage	I _C =10mA; I _B =0	400			V
V _{CE(sat-1)}	Collector-emitter saturation voltage	I _C =2A; I _B =0.4A			1.0	V
V _{CE(sat-2)}	Collector-emitter saturation voltage	I _C =5A; I _B =1.0A T _C =100 °C			2.0 3.0	V
V _{CE(sat-3)}	Collector-emitter saturation voltage	I _C =8A; I _B =2.0A			3.0	V
V _{BE(sat-1)}	Base-emitter saturation voltage	I _C =2A; I _B =0.4A			1.2	V
V _{BE(sat-2)}	Base-emitter saturation voltage	I _C =5A; I _B =1.0A T _C =100 °C			1.6 1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =700V; I _E =0 T _C =125 °C			0.1 1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =9V; I _C =0			0.1	mA
h _{FE-1}	DC current gain	I _C =2A; V _{CE} =5V	8		40	
h _{FE-2}	DC current gain	I _C =5A; V _{CE} =5V	5		30	
f _T	Transition frequency	I _C =0.5A; V _{CE} =10V; f=1MHz	4			MHz
C _{OB}	Collector outoutput capacitance	I _E =0; f=0.1MHz; V _{CB} =10V		80		pF

Switching times resistive load

t _d	Delay time	V _{CC} =125V, I _C =5A I _{B1} =-I _{B2} =1.0A t _p =25µs duty cycle≤1%			0.1	µs
t _r	Rise time				1.5	µs
t _s	Storage time				3.0	µs
t _f	Fall time				0.7	µs

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PACKAGE OUTLINE

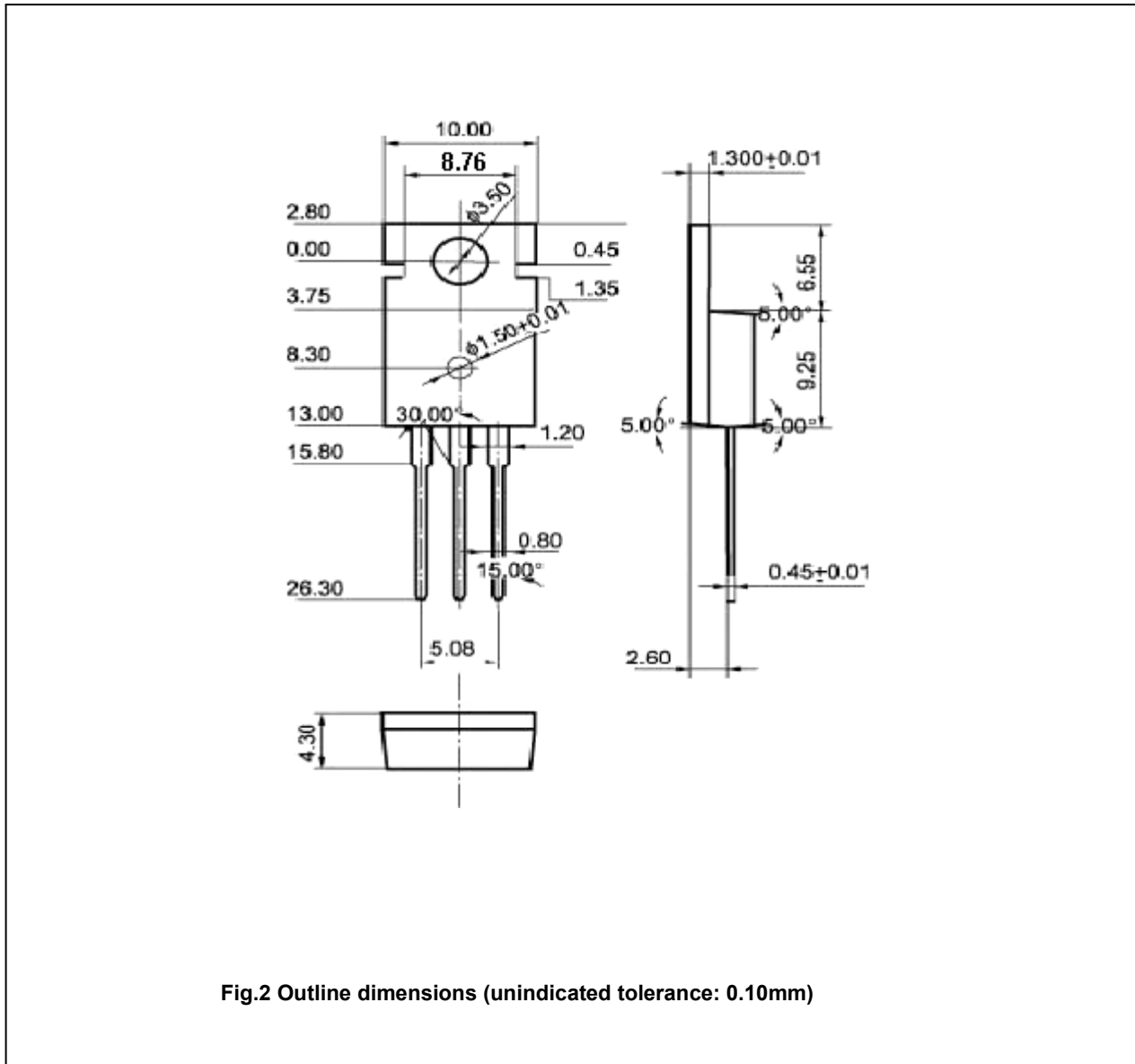


Fig.2 Outline dimensions (unindicated tolerance: 0.10mm)

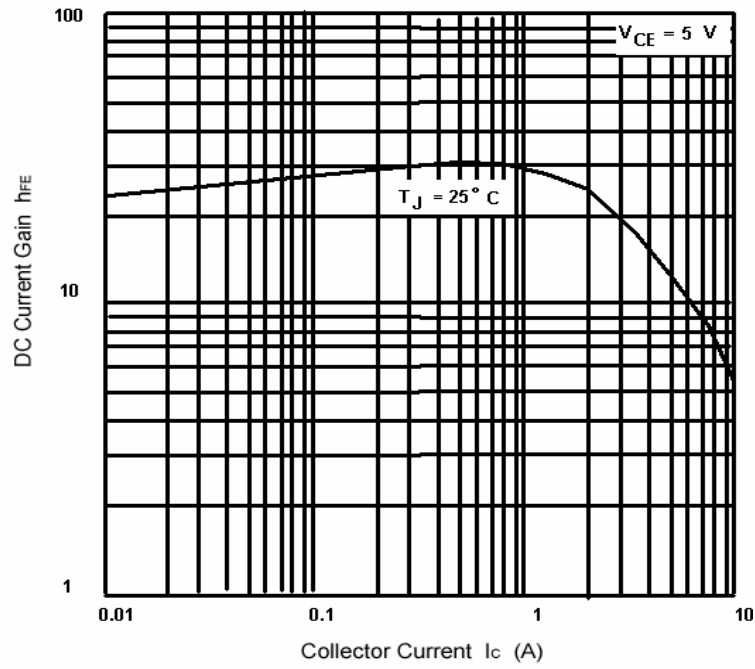


Fig.3 DC current Gain

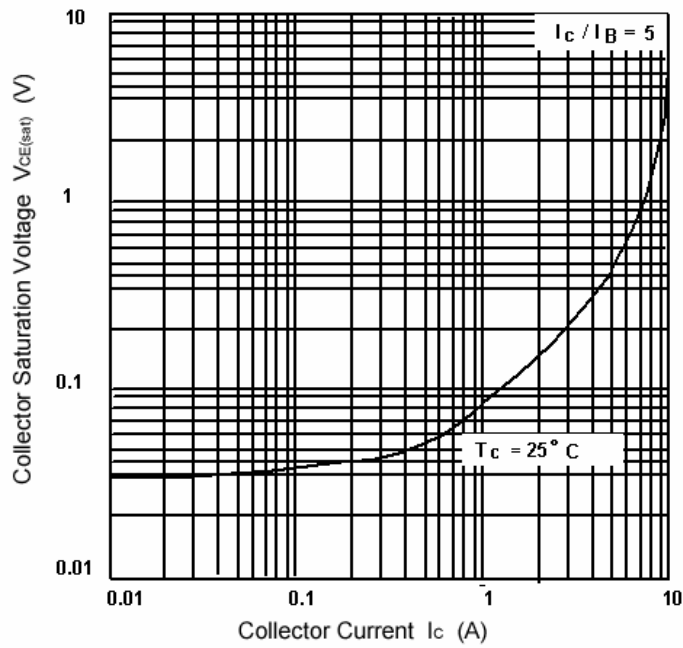


Fig.4 Collector-Emitter Saturation Voltage

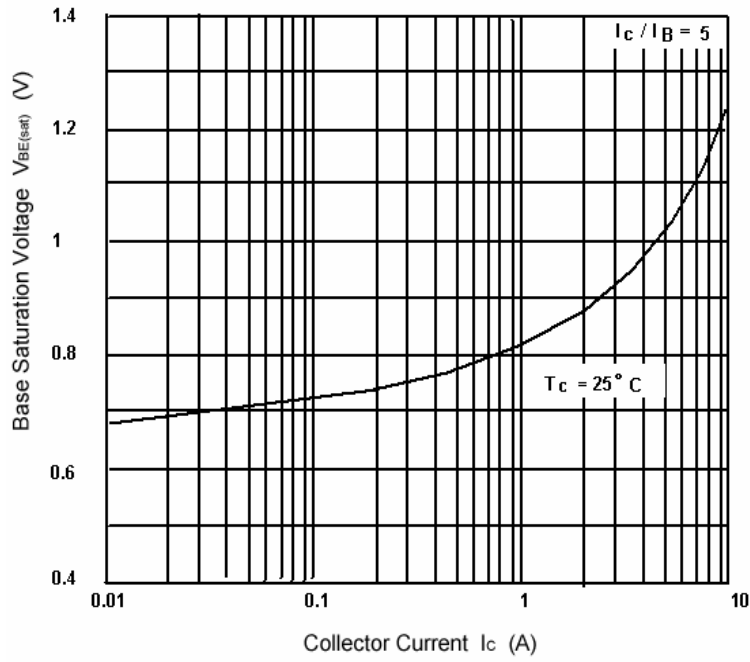


Fig.5 Base-Emitter Saturation Voltage

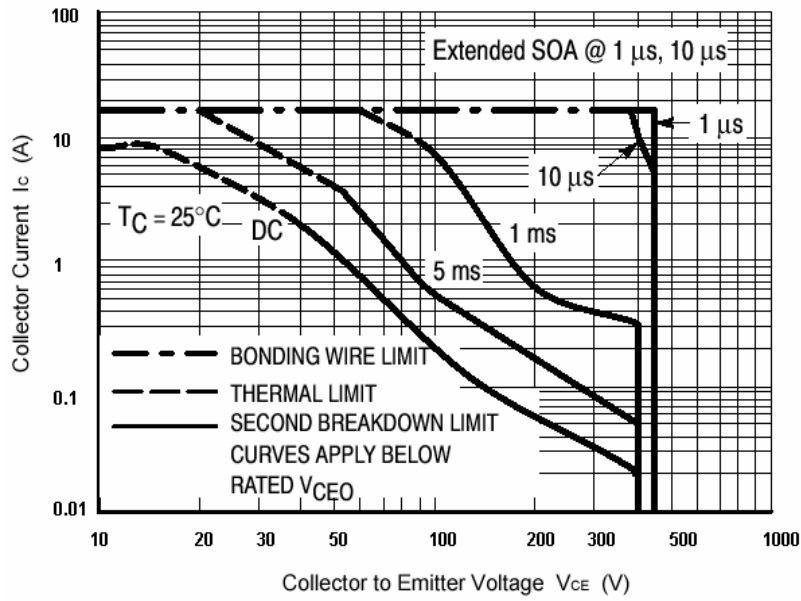


Fig.6 Safe Operating Area